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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **Naoto HORIGUCHI et al.**

Group Art Unit: **2811**

Serial No.: **09/726,386**

Examiner: **Thien F. TRAN**

Filed: **December 1, 2000**

Confirmation No.: **1274**

For: **SEMICONDUCTOR MEMORY WITH FLOATING GATE TYPE FET**

Attorney Docket No.: **001497**

Customer Number: **38834**

**AMENDMENT UNDER 37 C.F.R. §1.312**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 8, 2004

Sir:

Applicants received a Notice of Allowance dated **April 23, 2004** in connection with the above-identified application. It is respectfully requested that the following amendment be made to the claims of this application:

**Amendments to the Claims** begin on page 2 of this paper.

**Remarks** begin on page 8 of this paper.